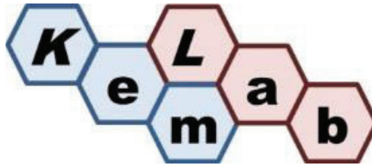


www.KemLab.com

KL NPR 20-30 micron FT – Sample

Negative photoresist

Sample Description

Thick straight wall negative photoresist for use with TMAH developer.

Viscosity ~830 cst

Processing

Coat: Spread Cycle: 10 sec spread cycle at 500 rpm

Spin Cycle: Accelerate at 1000 r/s to final spin speed for 45 seconds.

- For 20 micron Film = 750 rpm
- For 28 micron Film = 500 rpm

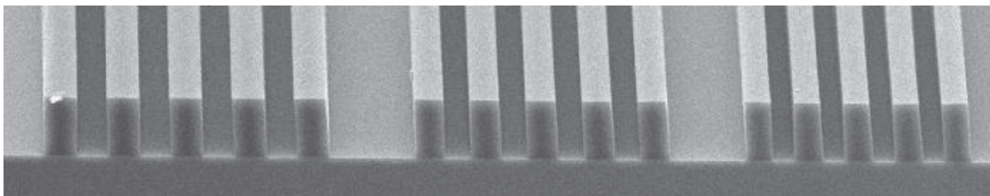
Soft-Bake: 110° C for 180 seconds (hotplate)

Exposure: Broadband exposure ~100 mJ/cm^2 on Silicon. Dose will vary on different substrates & exposure tools.

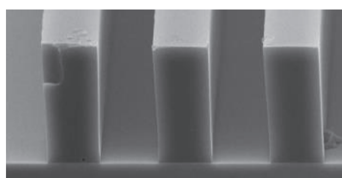
Post Exposure Bake: 110° C for 180 seconds (hotplate)

Develop: immersion in 0.26N TMAH developer ~ 5:00 minutes. (2 bath can yield improved results)

HardBake (if necessary): 110° C for 60 seconds (hotplate)



FT = 20 μm; 10,9,8 μm line/space



FT = 28 μm; 15 m lines